

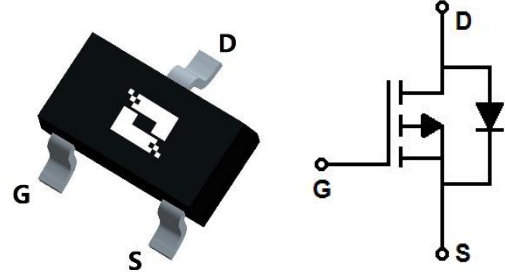
Features

- Low $R_{DS(on)}$ @ $V_{GS} = -4.5V$
- -3.3V Logic Level Control
- P Channel SOT23 Package
- Pb-Free, RoHS Compliant

$V_{(BR)DSS}$	$R_{DS(ON)}$ Typ	I_D Max
-20V	43m Ω @ -4.5V	-4.2A
	47m Ω @ -3.3V	

Applications

- Charging switch for portable devices
- Small brush-less DC motor drive
- Load Switch for Portable Devices
- DC-to-DC converters
- Power Management Functions


Order Information
SOT23

Product	Package	Marking	Packing
DW3415C	SOT23	3415C	3000PCS/Reel

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter		Rating	Unit
Common Ratings (TA=25°C Unless Otherwise Noted)				
VGS	Gate-Source Voltage		±12	V
V(BR)DSS	Drain-Source Breakdown Voltage		-20	V
TJ	Maximum Junction Temperature		150	°C
TSTG	Storage Temperature Range		-50 to 150	°C
Mounted on Large Heat Sink				
IDM	Pulse Drain Current Tested①	TA=25°C	-25	A
ID	Continuous Drain Current	TA=25°C	-4.2	A
		TA=70°C	-3.3	
PD	Maximum Power Dissipation	TA=25°C	1.25	W
		TA=70°C	1	
RQJA	Thermal Resistance Junction-Ambient		100	°C/W

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-20	—	—	V
I _{DSS}	Zero Gate Voltage Drain Current(T _A =25°C)	V _{DS} =-20V, V _{GS} =0V	—	—	-1	μA
	Zero Gate Voltage Drain Current(T _A =125°C)	V _{DS} =-16V, V _{GS} =0V	—	—	-100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	—	—	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.7	-1.2	V
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =-4.5V, I _D =-3A	—	43	52	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =-3.3V, I _D =-2A	—	47	58	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =-2.5V, I _D =-1A	—	55	68	mΩ
Dynamic Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	—	496	—	pF
C _{oss}	Output Capacitance		—	61	—	pF
C _{rss}	Reverse Transfer Capacitance		—	56	—	pF
Q _g	Total Gate Charge	V _{DS} =-10V I _D =-2A, V _{GS} =-4.5V	—	5.8	—	nC
Q _{gs}	Gate Source Charge		—	1.1	—	nC
Q _{gd}	Gate Drain Charge		—	1.68	—	nC
Switching Characteristics						
t _{d(on)}	Turn on Delay Time	V _{DD} =-10V, I _D =-2A, R _G =3.3Ω, V _{GS} =-4.5V	—	12	—	ns
t _r	Turn on Rise Time		—	6	—	ns
t _{d(off)}	Turn Off Delay Time		-	13	—	ns
t _f	Turn Off Fall Time		—	20	—	ns
Source Drain Diode Characteristics						
I _{SD}	Source drain current(Body Diode)	T _A =25°C	—	—	-4.2	A
V _{SD}	Forward on voltage②	T _J =25°C, I _{SD} =-2A, V _{GS} =0V	—	—	-1.2	V

Notes:

① Pulse width limited by maximum allowable junction temperature

②Pulse test ; Pulse width≤300μs, duty cycle≤2%.

Typical Characteristics

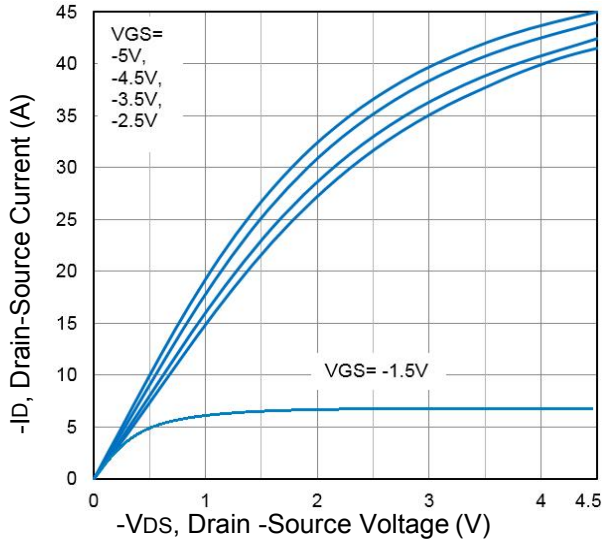


Fig1. Typical Output Characteristics

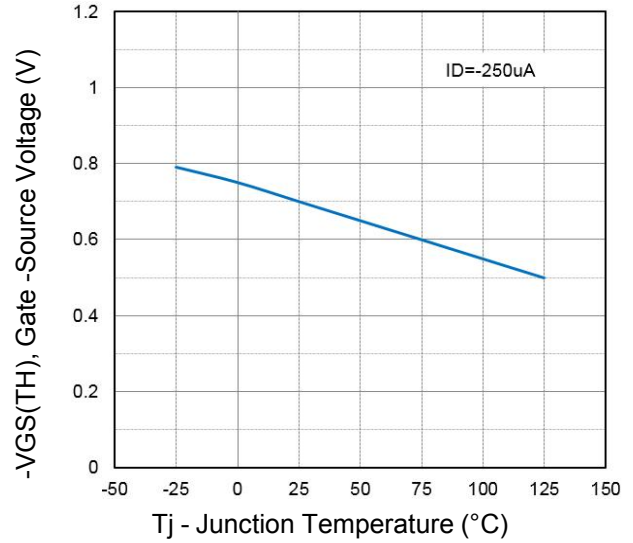


Fig2. Normalized Threshold Voltage Vs. Temperature

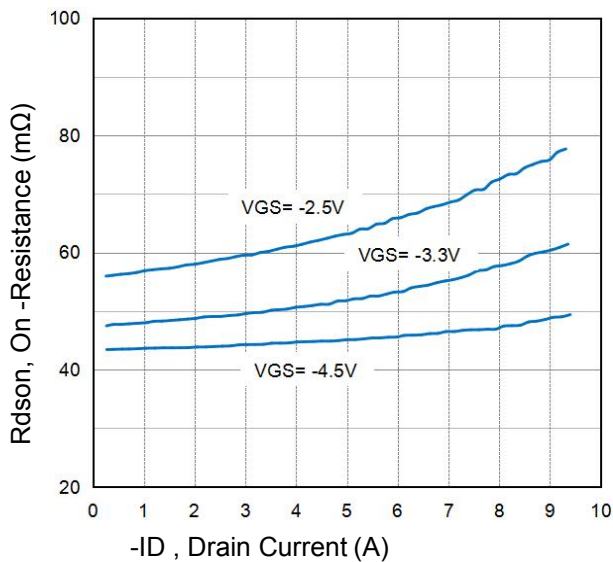


Fig3. On-Resistance vs. Drain Current and Gate Voltage

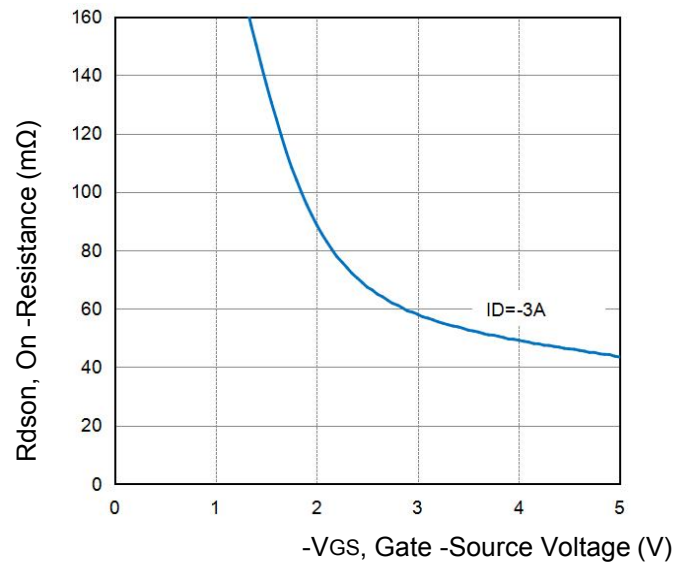


Fig4. On-Resistance vs. Gate Source Voltage

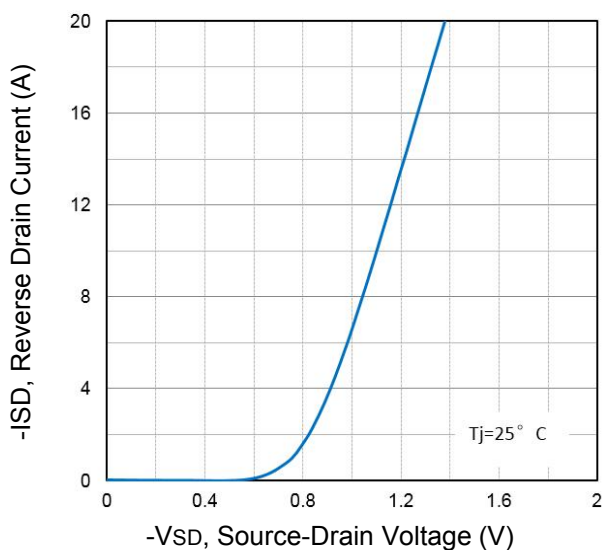


Fig5. Typical Source-Drain Diode Forward Voltage

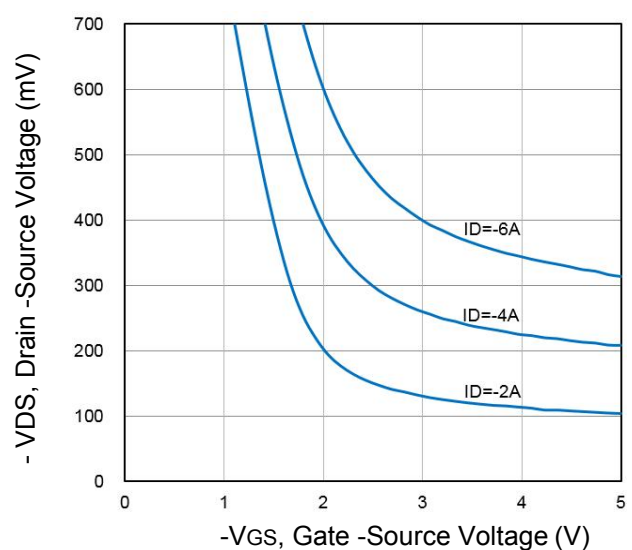


Fig6. Drain-Source Voltage vs Gate-Source Voltage

Typical Characteristics

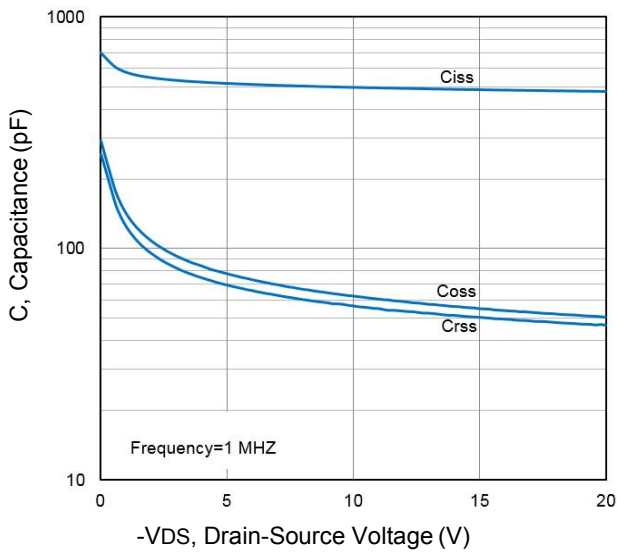


Fig7. Typical Capacitance Vs. Drain-Source Voltage

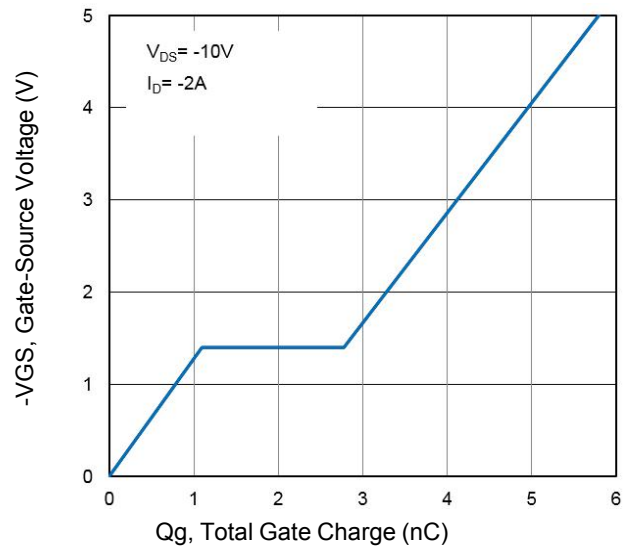


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

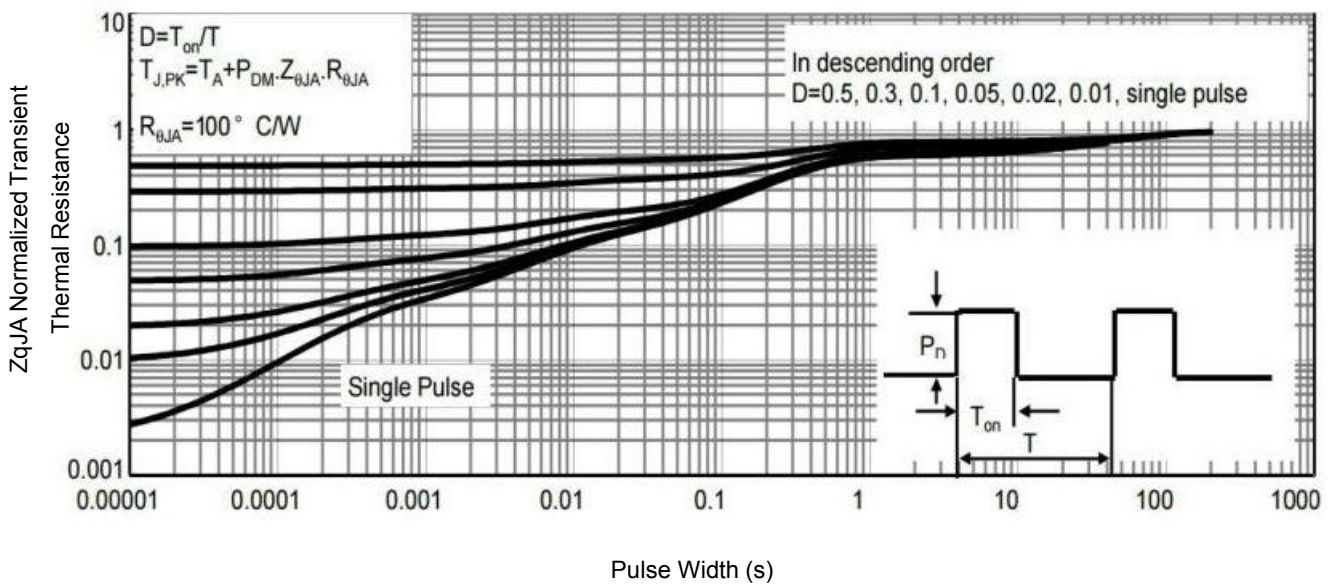


Fig9. Normalized Maximum Transient Thermal Impedance

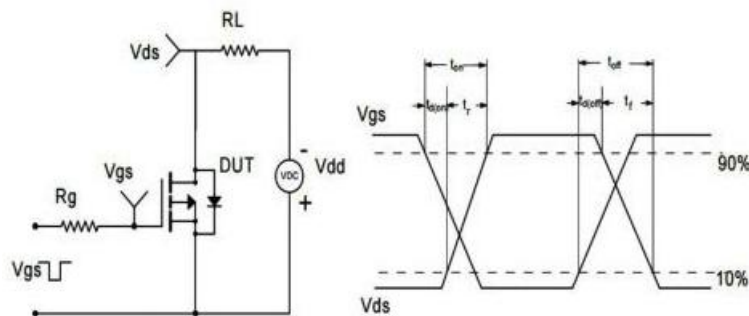
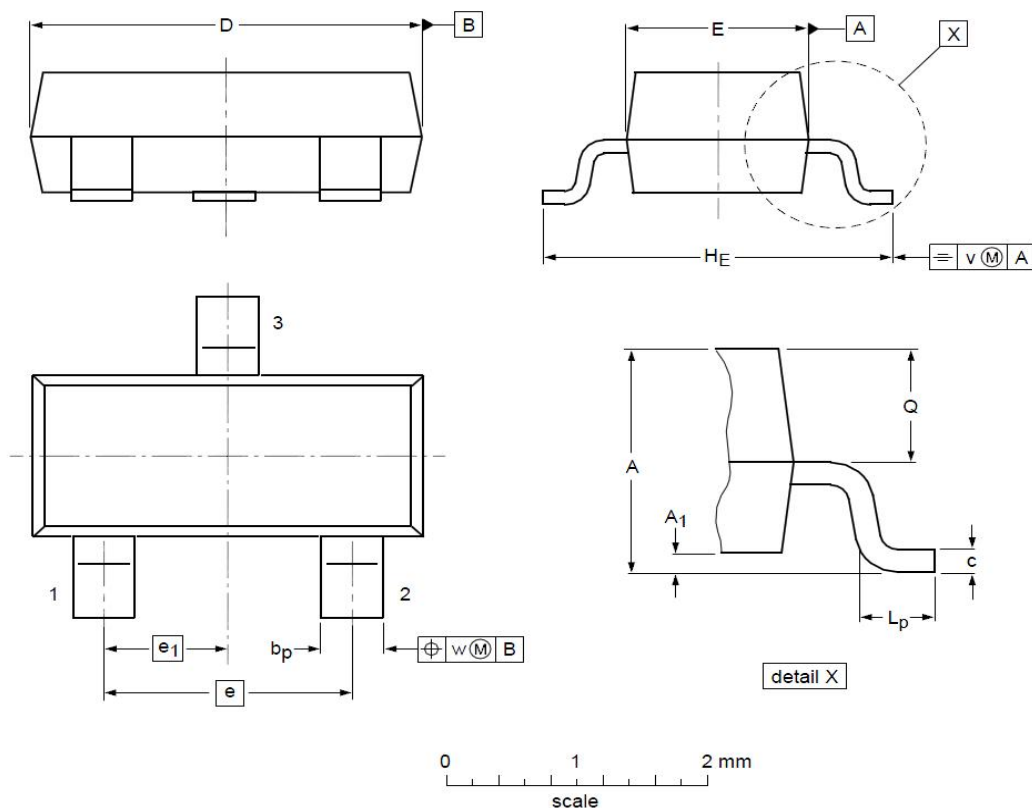


Fig10. Switching Time Test Circuit and waveforms

SOT23 Mechanical Data

DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	A₁	0.01	0.05	0.10
b_p	0.30	0.42	0.50	c	0.08	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
e	--	1.90	--	e₁	--	0.95	--
H_E	2.25	2.40	2.55	L_p	0.30	0.42	0.50
Q	0.45	0.49	0.55	v	--	0.20	--
w	--	0.10	--				

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